

Features

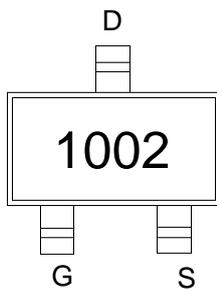
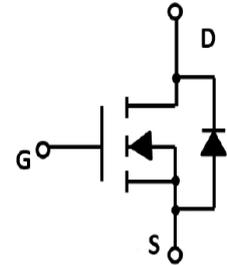
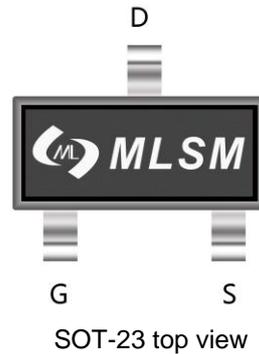
- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
100V	400mΩ@10V	2A
	500mΩ@4.5V	

Application

- DC-DC Converters
- Power management functions



1002: Device code

Marking and pin assignment



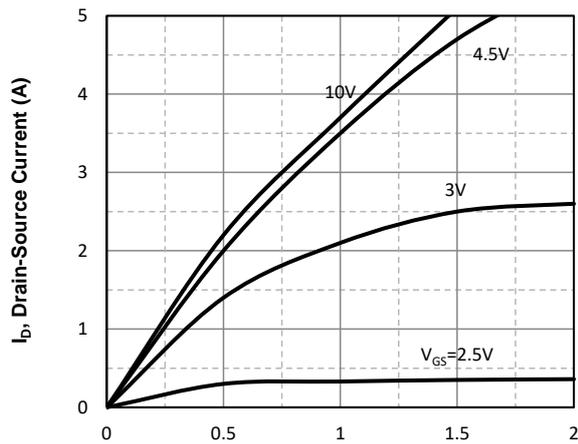
Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		100	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_c=25^\circ\text{C}$	2	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$	9	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	2	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	1.3	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		96	°C/W

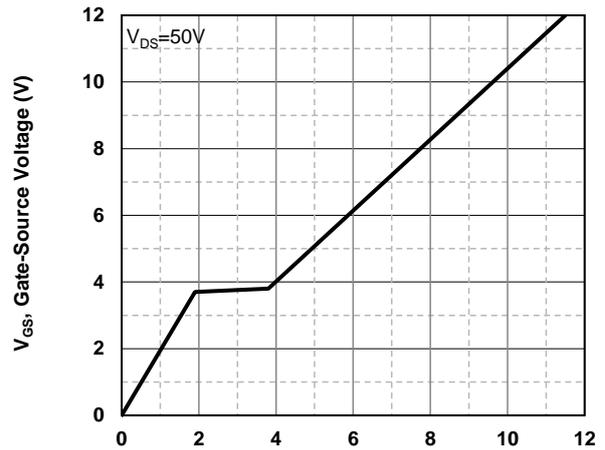
Ordering Information (Example)						
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS1002	SOT-23	1002	3,000	45,000	180,000	7"reel

Electrical Characteristics (T _J =25 °C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25 °C (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.8	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =2A	--	215	400	mΩ
		V _{GS} =4.5V, I _D =1A	--	260	500	mΩ
Dynamic Electrical Characteristics @ T_J = 25 °C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	387	--	pF
C _{OSS}	Output Capacitance		--	30	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	28	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =50V, I _D =2A, V _{GS} =10V	--	9.5	--	nC
Q _{gs}	Gate Source Charge		--	1.8	--	nC
Q _{gd}	Gate Drain Charge		--	2	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =50V, I _D =1.3A, V _{GS} =10V, R _G =1Ω	--	4	--	nS
t _r	Turn-on Rise Time		--	17.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	13	--	nS
t _f	Turn-Off Fall Time		--	28	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25 °C, I _S =2A	--	--	1.2	V

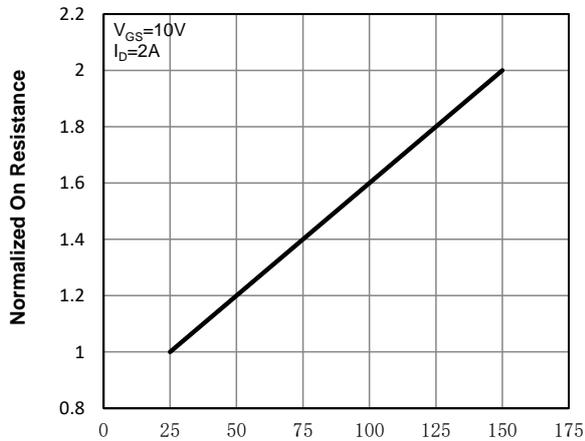
Typical Operating Characteristics



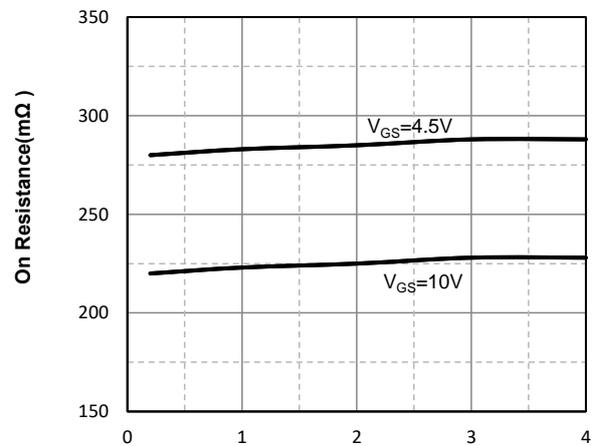
V_{DS} , Drain -Source Voltage (V)
Fig1. Typical Output Characteristics



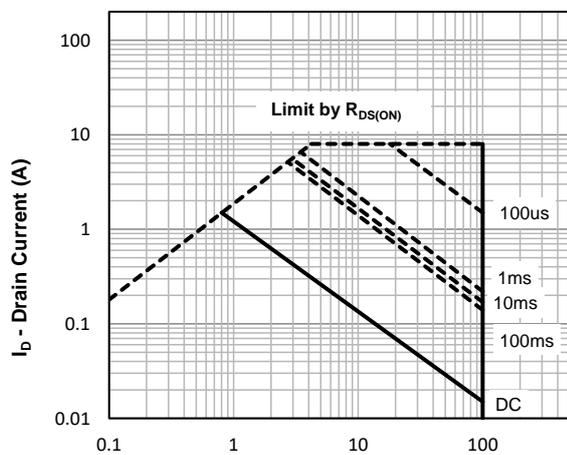
Q_g -Total Gate Charge (nC)
Fig2. Typical Gate Charge Vs. Gate-Source Voltage



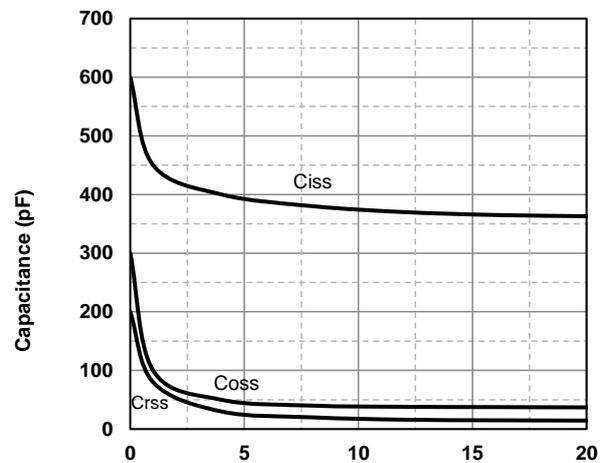
T_j - Junction Temperature ($^{\circ}C$)
Fig3. Normalized On-Resistance Vs. Temperature



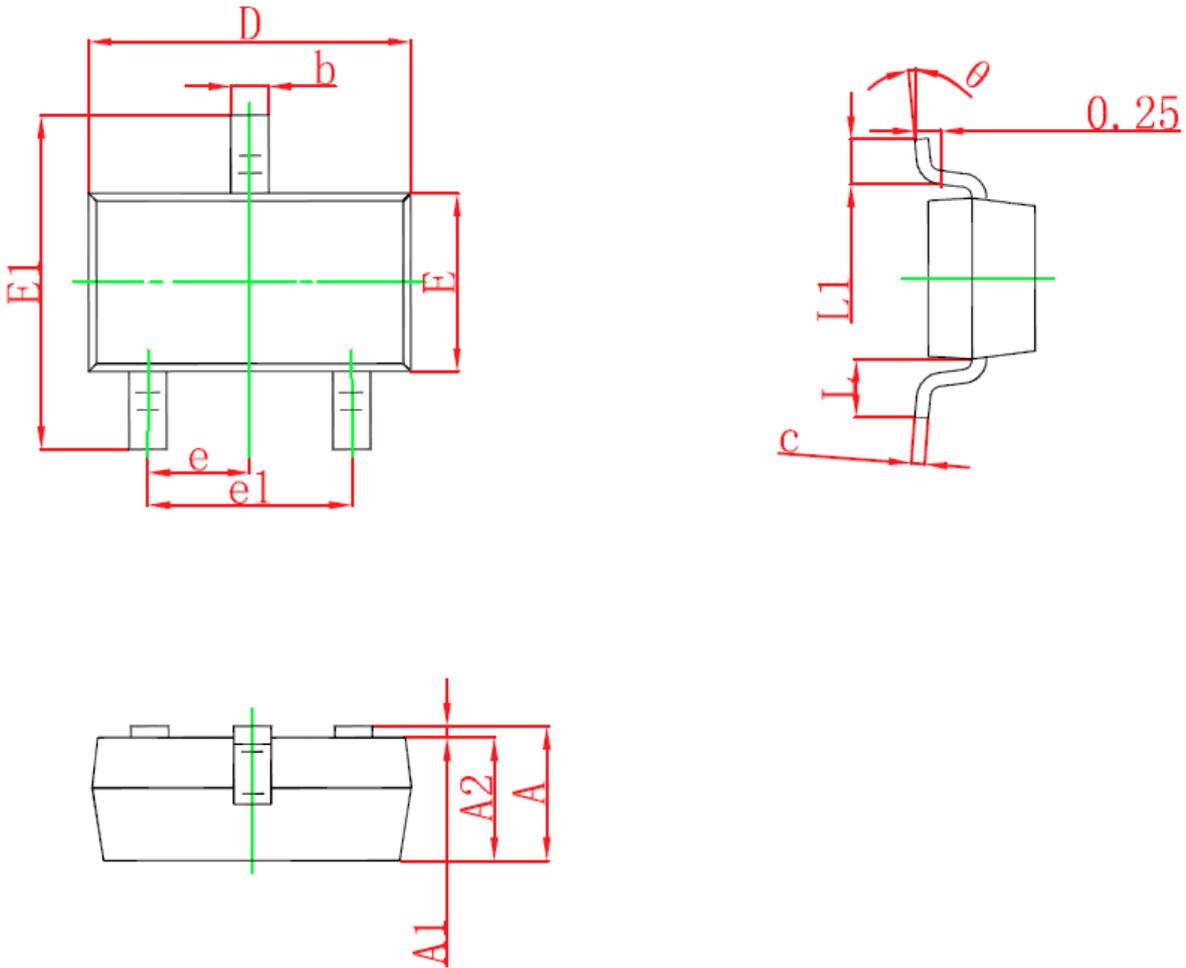
I_D , Drain-Source Current (A)
Fig4. On-Resistance Vs. Drain-Source Current



V_{DS} , Drain -Source Voltage (V)
Fig5. Maximum Safe Operating Area



V_{DS} , Drain-Source Voltage (V)
Fig6. Typical Capacitance Vs. Drain-Source Voltage

SOT-23 Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E1	2.250	2.550	0.088	0.100
E	1.200	1.400	0.047	0.055
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°